

JTDB25

25 Watts, 36 Volts, Pulsed Avionics, 960-1215 MHz

GENERAL DESCRIPTION The JTDB25 is a high power COMMON designed for pulsed systems in the frequency has gold thin-film metallization and diffu MTTF. The transistor includes input an capability. Low thermal resistance pack extends life.	CASE OUTLINE 55AW-1		
ABSOLUTE MAXIMUM RATING	GS		
Maximum Power Dissipation @ 25°C ¹	97W		
Maximum Voltage and Current			
$\mathrm{BV}_{\mathrm{CES}}$	55V		
$\mathrm{BV}_{\mathrm{EBO}}$	3.5V		
I_{C}	5.0A	_	
Maximum Temperatures			
Storage Temperature	-65 to +200°C		
Operating Junction Temperature	+200°C		

ELECTRICAL CHARACTERISTICS @ 25°C

SYMBOL	CHARACTERISTICS	TEST CONDITIONS	MIN	TYP	MAX	UNITS
BV_{EBO}	Emitter – Base Breakdown	$I_E = 5 \text{ mA}$	3.5			V
BV _{CES}	Collector – Emitter Breakdown	$I_C = 10 \text{ mA}$	55			V
h_{FE}	DC – Current Gain	$I_C = 500 \text{mA}, V_{CE} = 5 \text{V}$	20			
$\theta_{ m JC}^{-1}$	Thermal Resistance				1.8	°C/W

FUNCTIONAL CHARACTERISTICS @ 25°C

Pout	Power Output	F=960-1215 MHz	25			W
Pin	Power Input	Vcc = 36V			5	W
Gain	Power Gain	Pulse width = 10μs	7.0	7.5		
RL	Return Loss	DF=40%	8			dB
VSWR ²	Load Mismatch Tolerance	F = 1090 MHz			5:1	

NOTES: 1. At Rated Pulse Conditions 2. At Rated Output Power

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